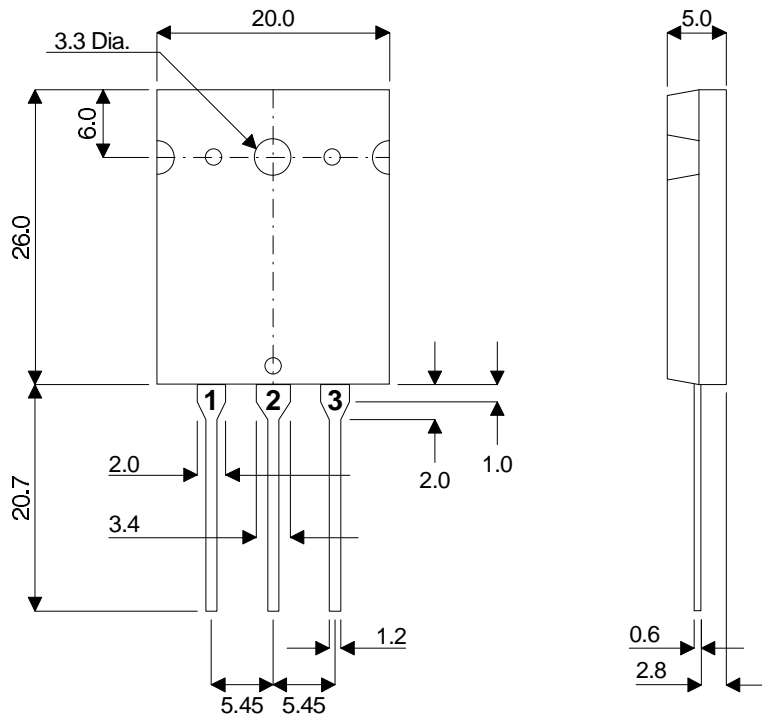


**MECHANICAL DATA**  
Dimensions in mm



**TO-3PBL**

Pin 1 – Gate

Pin 2 – Source  
Case is Source

Pin 3 – Drain

**N-CHANNEL**  
**POWER MOSFET**

**POWER MOSFETS FOR**  
**AUDIO APPLICATIONS**

**FEATURES**

- HIGH SPEED SWITCHING
- N-CHANNEL POWER MOSFET
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (160V & 200V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODE
- P-CHANNEL ALSO AVAILABLE AS BUZ905DP & BUZ906DP
- DOUBLE DIE PACKAGE FOR MAXIMUM POWER AND HEATSINK SPACE

**ABSOLUTE MAXIMUM RATINGS**

( $T_{case} = 25^{\circ}C$  unless otherwise stated)

		<b>BUZ900DP</b>	<b>BUZ901DP</b>
$V_{DSX}$	Drain – Source Voltage	160V	200V
$V_{GSS}$	Gate – Source Voltage	$\pm 14V$	
$I_D$	Continuous Drain Current	16A	
$I_{D(PK)}$	Body Drain Diode	16A	
$P_D$	Total Power Dissipation @ $T_{case} = 25^{\circ}C$	250W	
$T_{stg}$	Storage Temperature Range	$-55$ to $150^{\circ}C$	
$T_j$	Maximum Operating Junction Temperature	$150^{\circ}C$	
$R_{\theta JC}$	Thermal Resistance Junction – Case	$0.5^{\circ}C/W$	

**STATIC CHARACTERISTICS** ( $T_{case} = 25^{\circ}\text{C}$  unless otherwise stated)

Characteristic		Test Conditions		Min.	Typ.	Max.	Unit
BV <sub>DSX</sub>	Drain – Source Breakdown Voltage	V <sub>GS</sub> = -10V I <sub>D</sub> = 10mA	BUZ900DP	160			V
			BUZ901DP	200			
BV <sub>GSS</sub>	Gate – Source Breakdown Voltage	V <sub>DS</sub> = 0	I <sub>G</sub> = ±100μA	±14			V
V <sub>GS(OFF)</sub>	Gate – Source Cut-Off Voltage	V <sub>DS</sub> = 10V	I <sub>D</sub> = 100mA	0.1		1.5	V
V <sub>DS(SAT)*</sub>	Drain – Source Saturation Voltage	V <sub>GD</sub> = 0	I <sub>D</sub> = 16A			12	V
I <sub>DSX</sub>	Drain – Source Cut-Off Current	V <sub>GS</sub> = -10V	V <sub>DS</sub> = 160V BUZ900DP			10	mA
			V <sub>DS</sub> = 200V BUZ901DP			10	
yfs*	Forward Transfer Admittance	V <sub>DS</sub> = 10V	I <sub>D</sub> = 3A	1.4		4	S

**DYNAMIC CHARACTERISTICS** ( $T_{case} = 25^{\circ}\text{C}$  unless otherwise stated)

Characteristic		Test Conditions		Min.	Typ.	Max.	Unit
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 10V f = 1MHz			950		pF
C <sub>oss</sub>	Output Capacitance				550		
C <sub>rss</sub>	Reverse Transfer Capacitance				18		
t <sub>on</sub>	Turn-on Time	V <sub>DS</sub> = 20V I <sub>D</sub> = 7A			160		ns
t <sub>off</sub>	Turn-off Time				80		

\* Pulse Test: Pulse Width = 300μs , Duty Cycle ≤ 2%.

